

AMENDMENTS TO THE SPECIFICATION

At page 6 of the specification, at line 28, before the heading "DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS," please insert the following new paragraph:

FIG. 15 illustrates exemplary gate oxide thicknesses of transistors M1-M4 and transistors MP1, MP2, MN1, MN2 of Fig. 5.

Please replace the second full paragraph of page 13 with the following amended paragraph:

In the first embodiment, the gate oxide film of each of the MOS transistors M1 to M4 in the level conversion circuit 11 is thicker than the gate oxide film of each of the MOS transistors MP1, MP2, MN1, and MN2 in the differential amplification circuit 12, as shown in Fig. 15. Thus, the gate voltage capacity of the MOS transistors M1 to M4 is higher than the gate voltage capacity of the MOS transistors MP1, MP2, MN1, and MN2, as shown in Fig. 5. More specifically, the MOS transistors M1 to M4 of the level conversion circuit 11 have a gate voltage capacity of 2.5 V. The MOS transistors MP1, MP2, MN1, and MN2 of the differential amplification circuit 12 have a gate voltage capacity of 1.2 V.